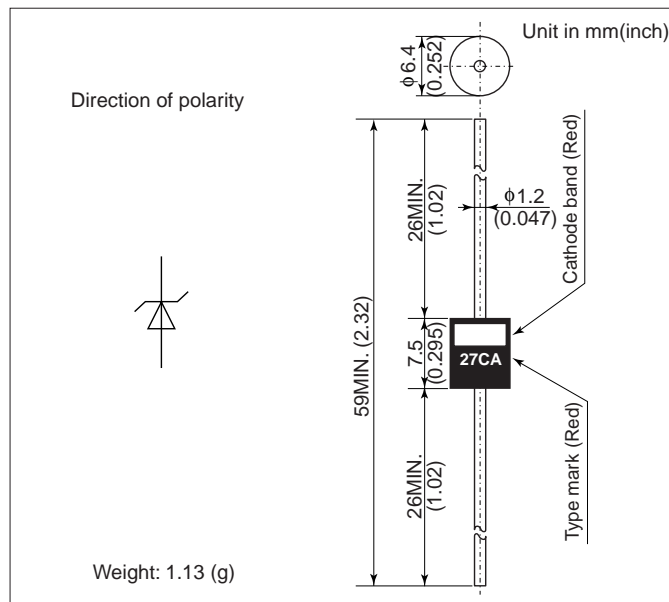


DAM3A

FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.
- Diffused-junction. Resin encapsulated.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

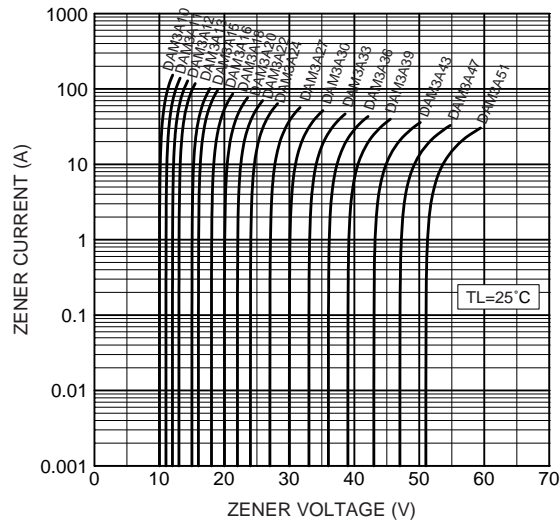
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	1800 (Rectangular pulse $t=0.1\text{ms}$ $T_i=25^\circ\text{C}$ start)
Operating Junction Temperature	T_j	$^\circ\text{C}$	$-40 \sim +150$
Storage Temperature	T_{stg}	$^\circ\text{C}$	$-40 \sim +150$
DC Reverse Voltage	V_{DC}	V	Refer to characteristics column

CHARACTERISTICS ($T_L=25^\circ\text{C}$)

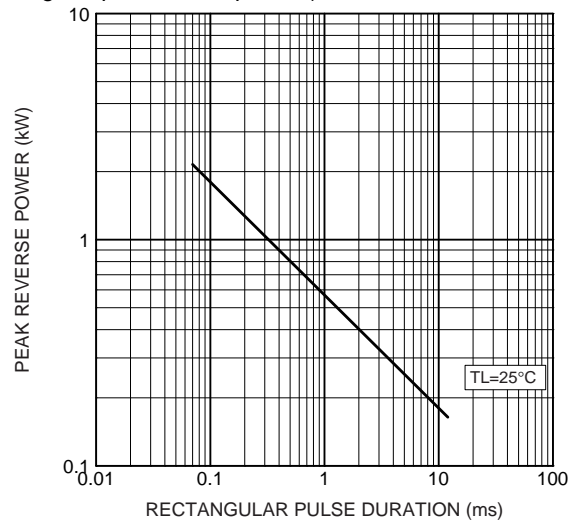
Type	DC Reverse Voltage V_{DC} (V)	Characteristics				Maximum Reverse Current	
		Zener Voltage V_Z (V)		Maximum Dynamic Impedance Z_z (ohm)	Test Current I_z (mA)		
		Minimum	Maximum			I_{RRM} (μ A)	V_R (V)
DAM3A10	7	9.4	10.6	15	75	50	7
DAM3A11	8	10.4	11.6	15	75	50	8
DAM3A12	9	11.4	12.7	15	75	50	9
DAM3A13	10	12.4	14.1	15	75	50	10
DAM3A15	11	13.5	15.6	15	75	50	11
DAM3A16	12	15.3	17.1	15	75	50	12
DAM3A18	13	16.8	19.1	15	45	50	13
DAM3A20	14	18.8	21.2	15	45	50	14
DAM3A22	16	20.8	23.3	15	45	50	16
DAM3A24	18	22.7	25.6	15	30	50	18
DAM3A27	20	25.1	28.9	15	30	50	20
DAM3A30	22	28.0	32.0	15	30	50	22
DAM3A33	24	31.0	35.0	15	30	50	24
DAM3A36	26	33.4	38.6	15	30	50	26
DAM3A39	28	36.1	41.9	15	30	50	28
DAM3A43	31	39.8	46.2	30	20	50	31
DAM3A47	34	43.3	50.7	30	20	50	34
DAM3A51	37	46.9	55.1	30	20	50	37

DAM3A

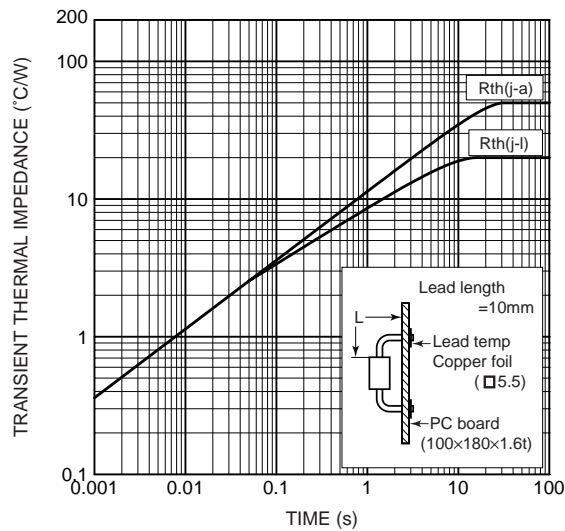
Typical zener characteristics



Typical reverse power characteristic
(Rectangular pulse non-repetitive)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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